

• General Description

The ZMS030N06F combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

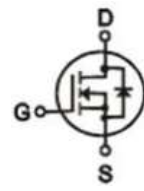
• Features

- Advance device constructure
- Low $R_{DS(ON)}$ to minimize conduction loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- Synchronous Rectification for AC-DC/DC-DC converter
- Oring switches
- Power Tools

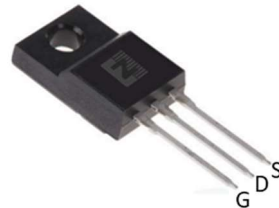
• Product Summary



$$V_{DS} = 60V$$

$$R_{DS(ON)} = 3m\Omega$$

$$I_D = 85A$$



TO-220F



• Ordering Information:

Part NO.	ZMS030N06F
Marking	ZMS030N06
Packing Information	Bulk Tube
Basic ordering unit (pcs)	1000

• Absolute Maximum Ratings ($T_c = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	85	A
	$I_{D@TC=75^\circ C}$	65	A
	$I_{D@TC=100^\circ C}$	54	A
Pulsed Drain Current ^①	I_{DM}	200	A
Total Power Dissipation($TC=25^\circ C$)	$P_{D@TC=25^\circ C}$	85	W
Total Power Dissipation($TA=25^\circ C$)	$P_{D@TA=25^\circ C}$	3	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy@ $L=0.1mH$	E_{AS}	245	mJ
Avalanche Current@ $L=0.1mH$	I_{AS}	70	A

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1.47	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	42	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.2	1.8	2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 60V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 30A$		3	3.9	m Ω
		$V_{GS} = 4.5V, I_D = 20A$		4.5	5.8	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 10V, I_D = 40A$		28		s
Source-drain voltage	V_{SD}	$I_S = 30A$			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$f = 1MHz$ $V_{DS} = 25V$	-	3500	-	pF
Output capacitance	C_{oss}		-	880	-	
Reverse transfer capacitance	C_{rss}		-	110	-	

•Gate Charge characteristics($T_a = 25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 25V$ $I_D = 15A$ $V_{GS} = 10V$	-	46	-	nC
Gate - Source charge	Q_{gs}		-	15	-	
Gate - Drain charge	Q_{gd}		-	7	-	

Note: ① Pulse Test : Pulse width $\leq 10\mu s$, Duty cycle $\leq 1\%$;

Fig.1 Gate-Charge Characteristics

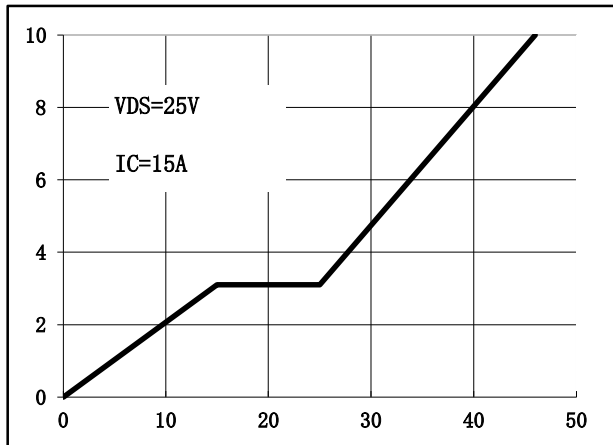


Fig.2 Capacitance Characteristics

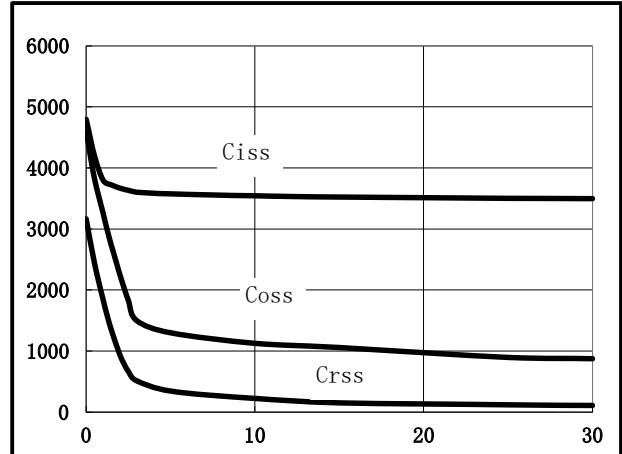


Fig.3 Power Dissipation

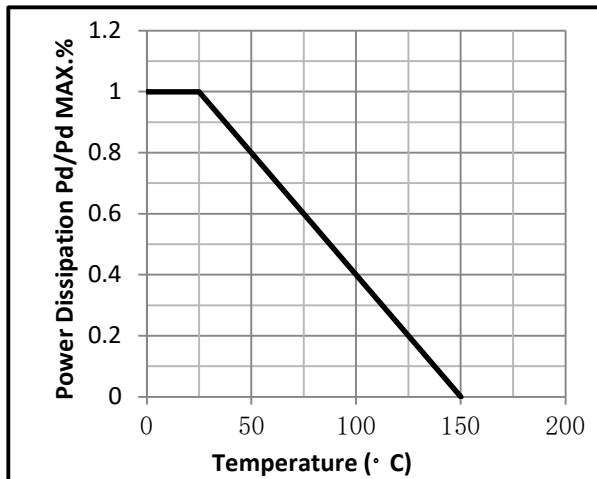


Fig.4 Typical output Characteristics

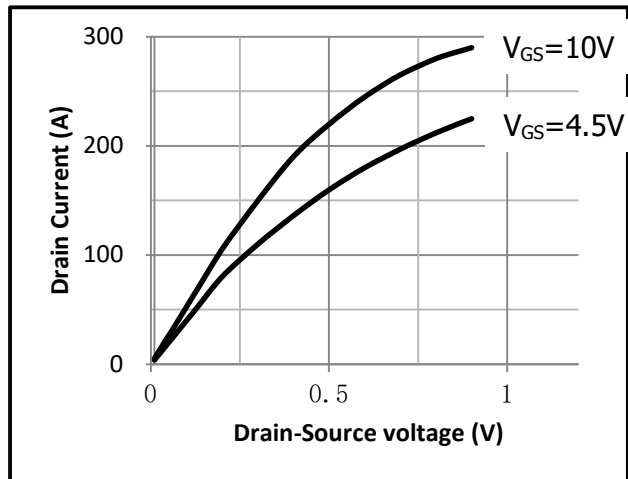


Fig.5 Threshold Voltage V.S Junction Temperature

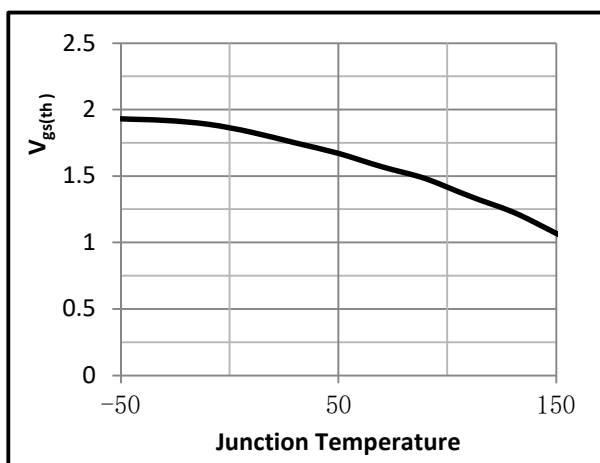


Fig.6 Resistance V.S Drain Current

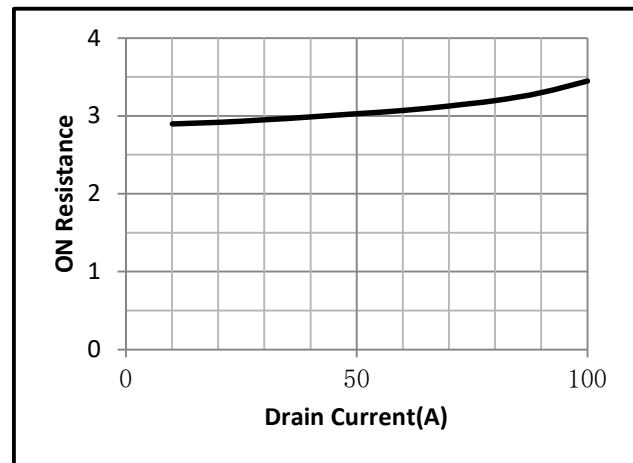


Fig.7 On-Resistance VS Gate Source Voltage

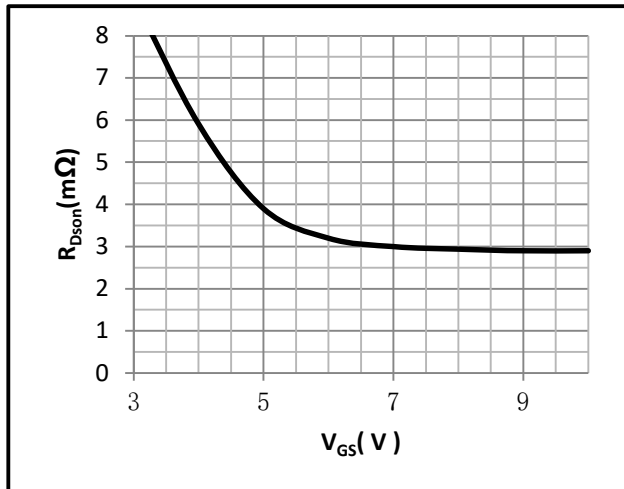


Fig.8 On-Resistance V.S Junction Temperature

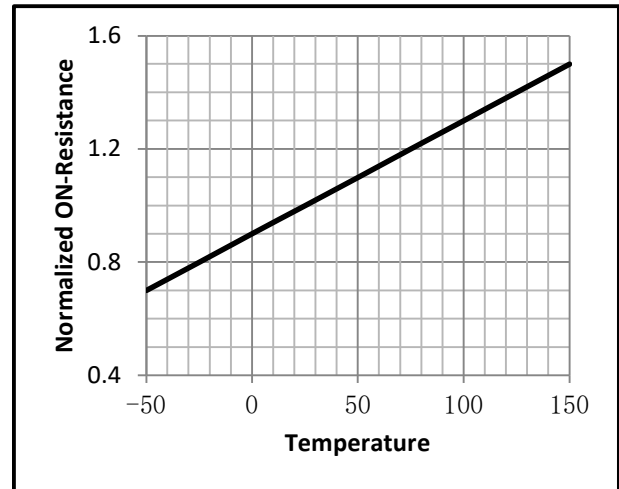


Fig.9 Switching Time Measurement Circuit

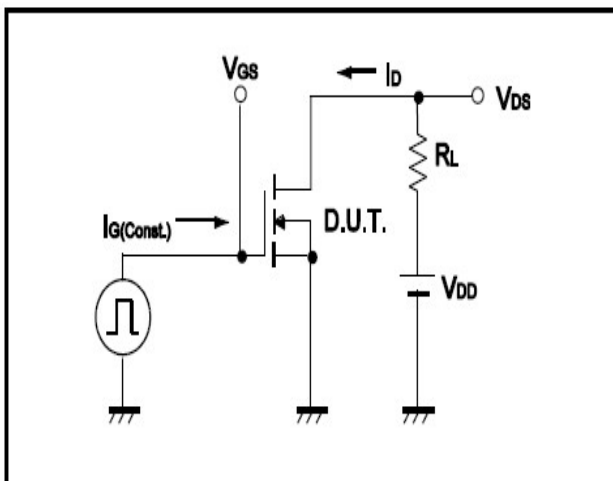


Fig.10 Gate Charge Waveform

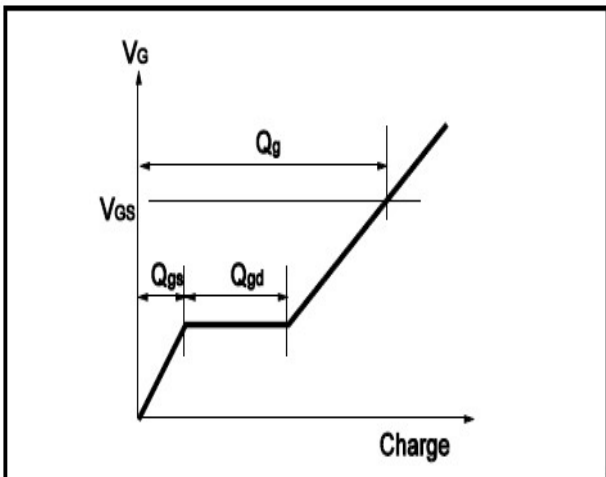


Fig.11 Switching Time Measurement Circuit

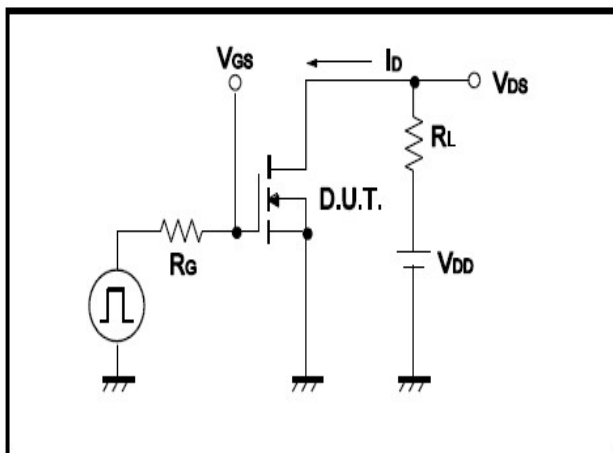
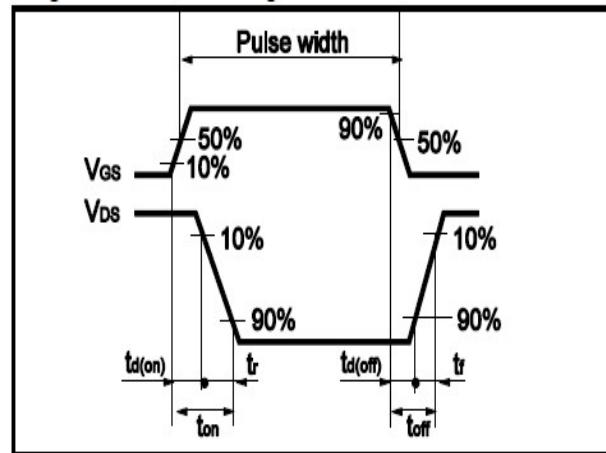


Fig.12 Gate Charge Waveform





• **Dimensions (TO-220F)**

Unit: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
C	4.5	4.9	b1	2.90	3.90
c	0.4	0.6	a	1.08	1.48
A	9.96	10.36	a1	0.70	0.90
B	15.67	16.07	E	2.34	2.74
B1	3.30	3.50	E1	2.34	2.74
R	3.08	3.28	C1	2.34	2.74
b	12.48	13.48	C2	2.56	2.96

